SMA5135

Features

- $\bullet \quad V_{(BR)DSS} ---- \pm 60 \; V \; (I_D = 100 \; \mu A) \\ \bullet \quad I_D ---- \pm 6A$
- $R_{DS(ON)}$ -----0.22 Ω max.
- Built-in three half bridge circuit configured by P-channel MOSFET and N-channel MOSFET
- ESD protection Zener with each Gate
- Compliant with RoHS directive

• Low On Resistance

Not to scale

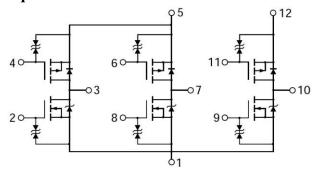
Applications

• 3-phase DC Motor Driver

Equivalent circuit

Package

SIP12 (SMA-12)



Absolute Maximum Ratings

Unless otherwise specified, $T_A = 25$ °C

Characteristic	Symbol	Test conditions	Rat		
			N-channel MOSFET	P-channel MOSFET	Unit
Drain to Source Voltage	V_{DSS}		60	-60	V
Gate to Source Voltage	V_{GSS}		±20	±20	V
Continuous Drain Current	I _{D(DC)}		6	-6	A
Pulsed Drain Current	I _{D(PULSE)}	PW ≤ 1 ms Duty cycle ≤25 %	10	-10	A
Maximum Allowable Power Dissipation	P_{T}	No.Fin Ta=25°C All Element Operation	4	W	
		Tc=25°C All Element Operation	2		
Thermal Resistance	θ_{j-a}	Junction-to-Ambient All Element Operation	31	°C/W	
	$\theta_{j\text{-}c}$	Junction-to-Case All Element Operation	4.31		°C/W
Channel Temperature	T_{ch}		1:	°C	
Storage Temperature	T_{stg}		-40 to 150		°C

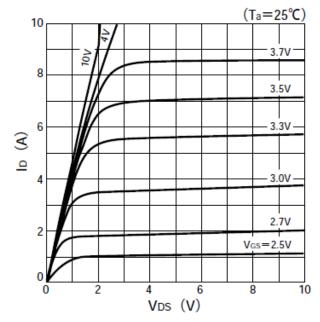
SMA5135

Electrical Characteristics

Unless otherwise specified, $T_A = 25$ °C

Unless otherwise specified, $T_A = 25$ Parameter		Test Conditions	Min	Tym	Mov	Unit
	Symbol	rest Conditions	Min.	Тур.	Max.	Unit
N-channel MOSFET Drain to Source Breakdown	1		1		Ι	
Voltage	$V_{(BR)DSS}$	$I_D = 100 \mu A, V_{GS} = 0 V$	60	_	_	V
Drain to Source Leakage Current	I_{DSS}	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$	_	_	100	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20 \text{ V}$	_	_	± 10	μΑ
Gate Threshold Voltage	V_{TH}	$V_{DS} = 10 \text{ V}, I_D = 250 \mu\text{A}$	1.0	_	2.0	V
Forward Transconductance	Re(y _{fs})	$V_{DS} = 10 \text{ V}, I_D = 3 \text{ A}$	_	5.5	_	S
Static Drain to Source On-State	R _{DS(ON)}	$I_D = 3 \text{ A}, V_{GS} = 4 \text{ V}$	_	_	0.22	Ω
Input Capacitance	C _{iss}	$V_{DS} = 10 \text{ V}$ $V_{GS} = 0 \text{ V}$ $f = 1 \text{ MHz}$	_	320	_	pF
Output Capacitance	C_{oss}		_	160		
Reverse Transfer Capacitance	C_{rss}		_	35	-	
Turn-On Delay Time	t _{d(on)}		_	16	_	ns
Rise Time	t _r	$V_{DD} \stackrel{.}{=} 20 \text{ V}$ $I_D = 3 \text{ A}$ $V_{GS} = 5 \text{ V}, R_L = 6.67 \Omega$	_	65	_	
Turn-Off Delay Time	t _{d(off)}		_	70	_	
Fall Time	t_{f}		_	45	_	
Source to Drain Diode Forward Voltage	V_{SD}	$I_S = 6A, V_{GS} = 0 V$	_	1.2	_	V
Source to Drain Diode Reverse Recovery Time	t _{rr}	$I_{SD} = 3 \text{ A}, V_{GS} = 0 \text{ V}$ di/dt = 100 A/ μ s	_	65	_	ns
P-channel MOSFET						
Drain to Source Breakdown Voltage	V _{(BR)DSS}	$I_D = -100 \ \mu A, \ V_{GS} = 0 \ V$	- 60	_	_	V
Drain to Source Leakage Current	I_{DSS}	$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}$	_	_	- 100	μΑ
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20 \text{ V}$	_	_	± 10	μA
Gate Threshold Voltage	V_{TH}	$V_{DS} = -10 \text{ V}, I_{D} = -250$ μA	- 1.0	_	- 2.0	V
Forward Transconductance	Re(y _{fs})	$V_{DS} = -10 \text{ V}, I_D = -3 \text{ A}$	_	6.0	_	S
Static Drain to Source On-State	R _{DS(ON)}	$I_D = -3 \text{ A}, V_{GS} = -10 \text{ V}$	_	_	0.22	Ω
Input Capacitance	C _{iss}	$V_{DS} = -10 \text{ V}$ $V_{GS} = 0 \text{ V}$ $f = 1 \text{ MHz}$	_	790	_	pF
Output Capacitance	C _{oss}		_	310	_	
Reverse Transfer Capacitance	C _{rss}		-	90	_	
Turn-On Delay Time	t _{d(on)}	$V_{DD} \rightleftharpoons 20 \text{ V}$ $I_D = -3 \text{ A}$ $V_{GS} = -5 \text{ V}, R_L = 6.67 \Omega$	-	40	_	ns
Rise Time	t _r		-	110	_	
Turn-Off Delay Time	$t_{d(off)}$		-	160	_	
Fall Time	t_{f}		_	80	_	
Source to Drain Diode Forward Voltage	V_{SD}	$I_S = -6A, V_{GS} = 0 V$	_	- 1.1	_	V
Source to Drain Diode Reverse Recovery Time	t _{rr}	$I_{SD} = -3 \text{ A}, V_{GS} = 0 \text{ V}$ di/dt = 100 A/ μ s	_	85	_	ns

Typical Characteristics



 $Figure \ 1 \quad I_D \ vs. \ V_{DS} \ Characteristics \ (N\text{-}channel)$

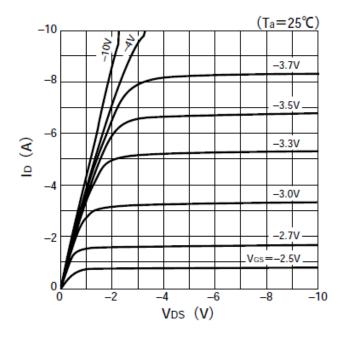


Figure 2 I_D vs. V_{DS} Characteristics (P-channel)

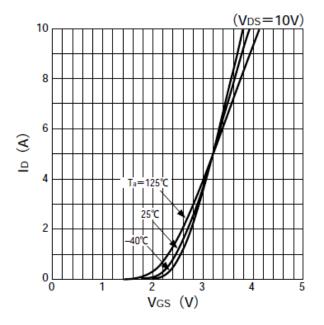


Figure 3 I_D vs. V_{GS} Characteristics (N-channel)

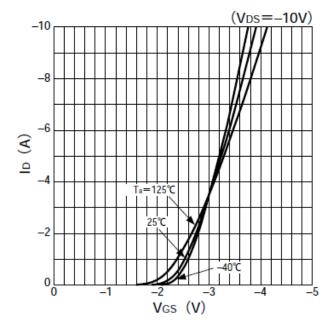


Figure 4 I_D vs. V_{GS} Characteristics (P-channel)

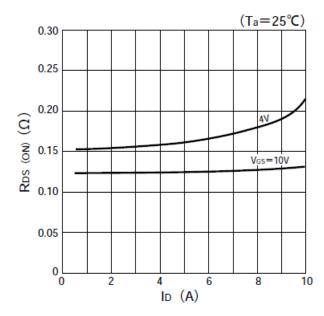


Figure 5 $R_{DS(ON)}$ vs. I_D Characteristics (N-channel)

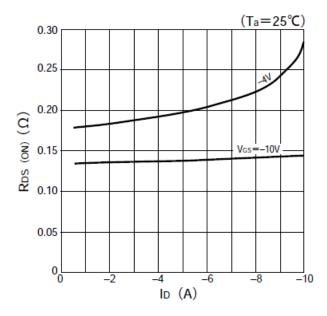
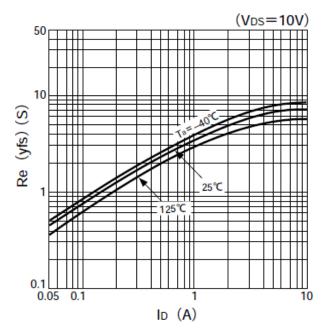
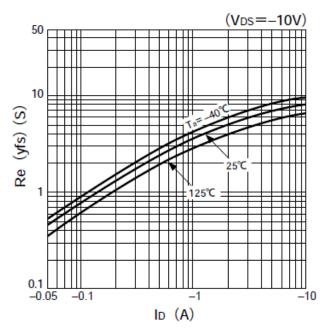


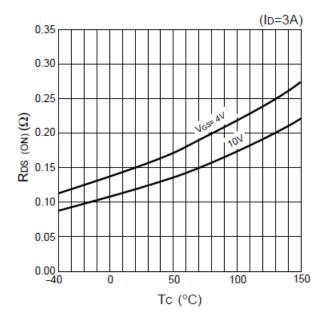
Figure 6 R_{DS(ON)} vs. I_D Characteristics (P-channel)

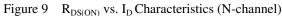


 $Figure \ 7 \quad R_{e(yfs)} \ vs. \ I_D \ Characteristics \ (N\text{-}channel)$



 $Figure \ 8 \quad R_{e(yfs)} \ vs. \ I_D \ Characteristics \ (P\text{-channel})$





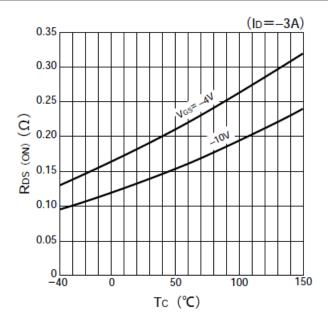


Figure 10 R_{DS(ON)} vs. I_D Characteristics (P-channel)

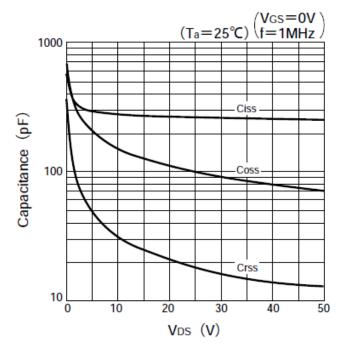


Figure 11 Capacitance vs. V_{DS} Characteristics (N-channel)

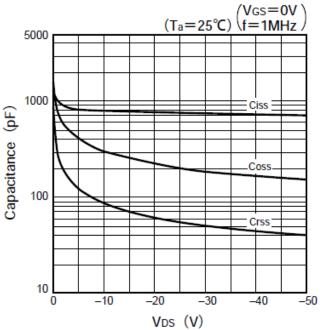


Figure 12 Capacitance vs. V_{DS} Characteristics (P-channel)

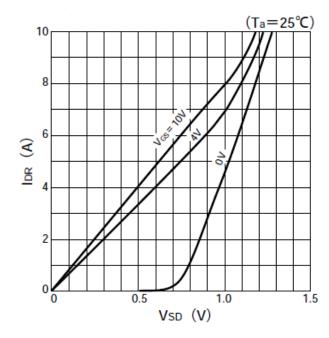


Figure 13 I_{DR} vs. V_{SD} Characteristics (N-channel)

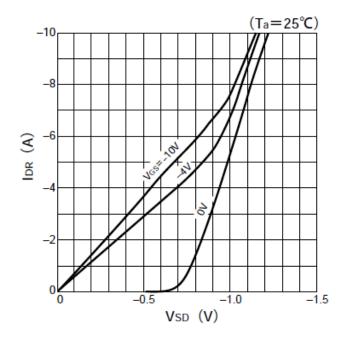


Figure 14 I_{DR} vs. V_{SD} Characteristics (P-channel)

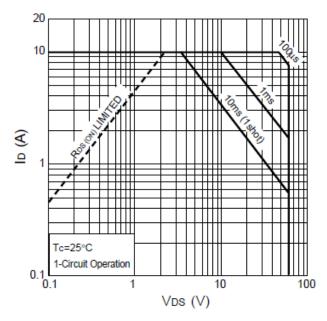


Figure 15 Safe Operating Area (N-channel)

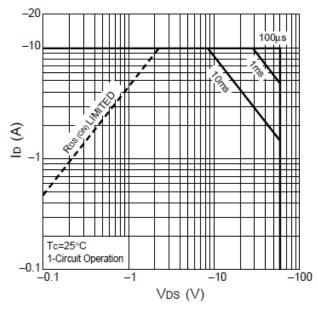


Figure 16 Safe Operating Area (P-channel)

Derating Curve

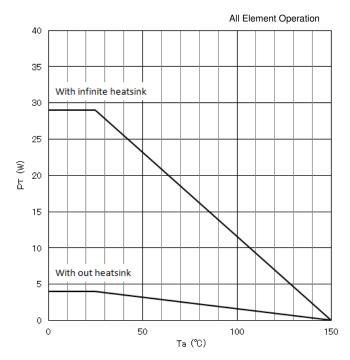
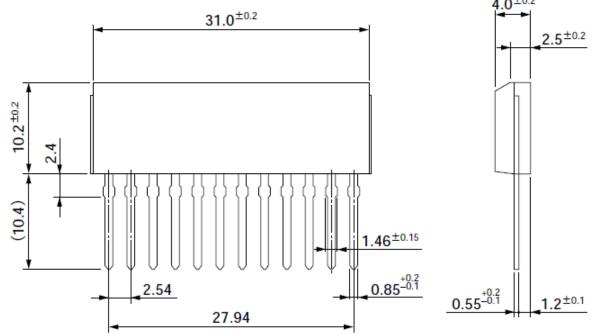


Figure 17 P_T vs. T_A Derating Curve

Package Outline

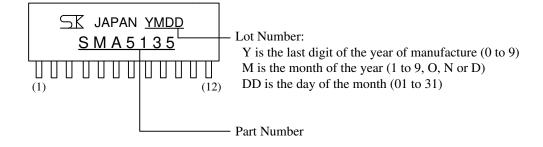
• SIP12(SMA-12)



NOTES:

- Dimension is in millimeters.
- Pin treatment Pb-free. Device composition compliant with the RoHS directive.

Marking Diagram



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